

**MS1261**

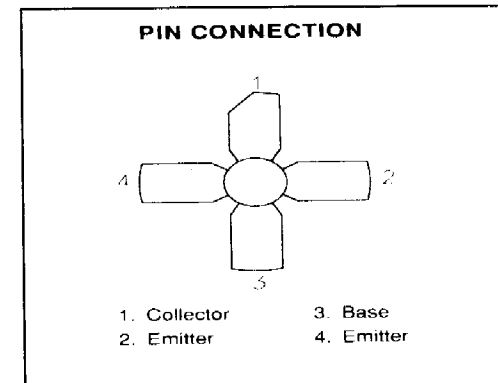
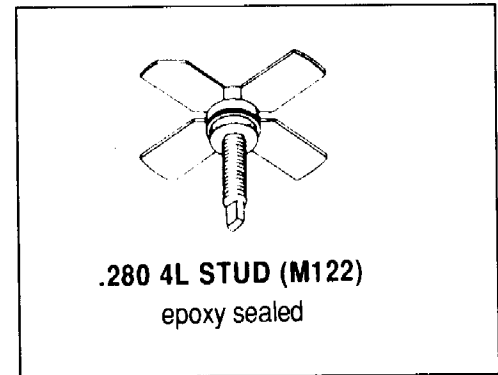
**RF & MICROWAVE TRANSISTORS  
VHF MOBILE APPLICATIONS**

**Features**

- 175 MHz
- 12.5 VOLTS
- P<sub>OUT</sub> = 15 WATTS
- G<sub>p</sub> = 12 dB MINIMUM
- INPUT IMPEDANCE MATCHING
- COMMON EMITTER CONFIGURATION

**DESCRIPTION:**

The MS1261 is a Class C 12.5V epitaxial silicon NPN planar transistor designed primarily for UHF communications. This device utilizes a gold metallized, emitter ballasted die geometry for superior reliability and infinite VSWR capability.



**ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)**

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	36	V
V <sub>CEO</sub>	Collector-Emitter Voltage	18	V
V <sub>CES</sub>	Collector-Emitter Voltage	36	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>c</sub>	Device Current	2.5	A
P <sub>DISS</sub>	Power Dissipation	34	W
T <sub>J</sub>	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

**Thermal Data**

R <sub>TH(J-C)</sub>	Thermal Resistance Junction-case	8.75	°C/W
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**ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)**

**STATIC**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV <sub>CES</sub>	I <sub>C</sub> = 50 mA      V <sub>BE</sub> = 0V	36	---	---	V
BV <sub>CEO</sub>	I <sub>C</sub> = 15 mA	18	---	---	V
BV <sub>EBO</sub>	I <sub>E</sub> = 2.5 mA      I <sub>C</sub> = 0mA	4.0	---	---	V
I <sub>CBO</sub>	V <sub>CE</sub> = 15 V      I <sub>E</sub> = 0mA	---	---	1	mA
H <sub>FE</sub>	V <sub>CE</sub> = 5 V      I <sub>C</sub> = 250mA	20	---	200	---

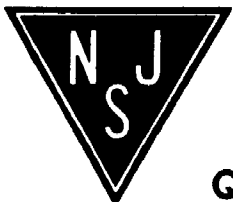
**DYNAMIC**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P <sub>OUT</sub>	f = 175 MHz      P <sub>IN</sub> = 1W      V <sub>CE</sub> = 12.5V	15	---	---	W
η <sub>c</sub>	f = 175 MHz      P <sub>IN</sub> = 1W      V <sub>CE</sub> = 12.5V	60	---	---	%
G <sub>p</sub>	f = 175 MHz      P <sub>IN</sub> = 1W      V <sub>CE</sub> = 12.5V	12	---	---	dB
C <sub>OB</sub>	f = 1 MHz      V <sub>CB</sub> = 12.5V	---	---	45	pf

**IMPEDANCE DATA**

FREQ	Z <sub>IN</sub> (Ω)	Z <sub>CL</sub> (Ω)
175 MHz	1.2 - j0.4	5.2 + j1.1

P<sub>OUT</sub> = 15W  
 V<sub>CC</sub> = 12.5V



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**PACKAGE MECHANICAL DATA**

